



### 100V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-100V	350mΩ @ V <sub>GS</sub> = -10V	-1.6A
-1007	450mΩ @ V <sub>GS</sub> = -6V	-1.4A

## **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

## Features and Benefits

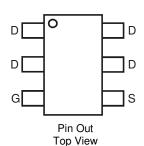
- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

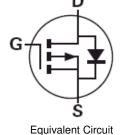
### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.018 grams (Approximate)









### Ordering Information (Note 4)

Part Number	Part Number Compliance		Packaging
ZXMP10A17E6TA	Standard	SOT26	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

SOT26

 $\begin{array}{l} 1A17 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ C=2015) \\ M\ or\ \overline{M} = Month\ (ex:\ 9=September) \end{array}$ 

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	E	F	G	Н		J	K	L	М	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

(	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-100	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 6)		-1.6	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I <sub>D</sub>	-1.3	Α
		(Note 5)		-1.3	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 7)	I <sub>DM</sub>	-7.7	Α
Continuous Source Current (Body Diode) (No		(Note 6)	Is	-2.1	A
Pulsed Source Current (Bod	y Diode)	(Note 7)	I <sub>SM</sub>	-7.7	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	0	1.1 8.8	w
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.7 13.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 5)	р	113	°C/W
Thermal nesistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	73	G/VV
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

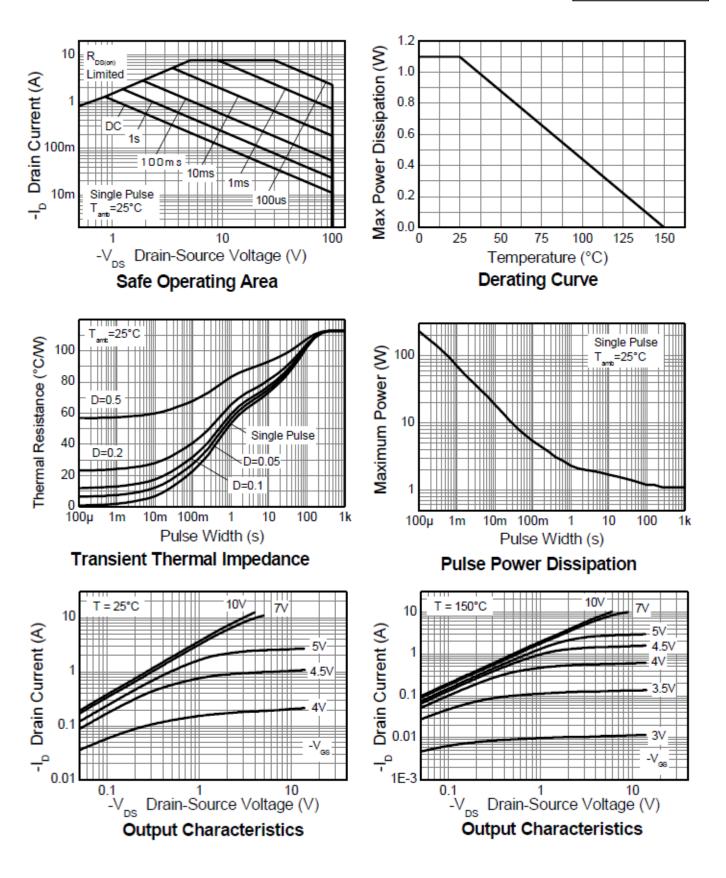
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test C	Condition
OFF CHARACTERISTICS	•					•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	_	_	V	$I_D = -250 \mu A, V_G$	s = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -100V, V_0$	<sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{D}$	s = 0V
ON CHARACTERISTICS	•					•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	-2	_	-4	V	$I_D = -250 \mu A, \ V_D$	s = V <sub>G</sub> s
Static Drain Source On Registeres (Note 9)	Б			0.35	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> =	-1.4A
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(ON)</sub>			0.45	1 12	V <sub>GS</sub> = -6V, I <sub>D</sub> = -1.2A	
Forward Transconductance (Notes 8 & 9)	g <sub>fs</sub>	_	2.8	_	S	$V_{DS} = -15V, I_{D} =$	: -1.4A
Diode Forward Voltage (Note 8)	$V_{SD}$	_	-0.85	-0.95	V	I <sub>S</sub> = -1.7A, V <sub>GS</sub>	= 0V
Reverse Recovery Time (Note 9)	t <sub>rr</sub>		33	_	ns	-I <sub>S</sub> = -1.5A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 9)	Q <sub>rr</sub>	_	48	_	nC	$I_S = -1.5A$ , $al/at$	= 100A/μS
DYNAMIC CHARACTERISTICS (Note 9)			•	•	•	•	
Input Capacitance	C <sub>iss</sub>	_	424	_	pF	501/1/	01/
Output Capacitance	Coss	_	36.6	_	pF	V <sub>DS</sub> = -50V, V <sub>G</sub> ; −F = 1MHz	S = UV
Reverse Transfer Capacitance	C <sub>rss</sub>	_	29.8	_	pF	1 = 1101112	
Total Gate Charge (Note 10)	Qg	_	7.1	_	nC	V <sub>GS</sub> = -6V	
Total Gate Charge (Note 10)	Qg	_	10.7	_	nC		V <sub>DS</sub> = -50V
Gate-Source Charge (Note 10)	Q <sub>gs</sub>	_	1.7	_	nC	$V_{GS} = -10V$	$I_D = -1.4A$
Gate-Drain Charge (Note 10)	Q <sub>gd</sub>	_	3.8	_	nC		
Turn-On Delay Time (Note 10)	t <sub>D(on)</sub>	_	3	_	ns		•
Turn-On Rise Time (Note 10)	t <sub>r</sub>		3.5	_	ns	V <sub>DD</sub> = -50V, V <sub>GS</sub> = -10V	
Turn-Off Delay Time (Note 10)	t <sub>D(off)</sub>		13.4	_	ns	$I_D = -1A$ , $R_G \cong 6$	Ω
Turn-Off Fall Time (Note 10)	t <sub>f</sub>	_	7.2	_	ns	1	

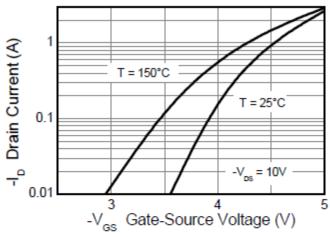
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at  $t \le 5$  sec.
- 7. Same as Note 5, except the device is pulsed with D = 0.05 and pulse width 10μs. The pulse current is limited by the maximum junction temperature.
- 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s; duty cycle  $\leq$  2%.
- 9. For design aid only, not subject to production testing.
- 10. Switching characteristics are independent of operating junction temperatures.

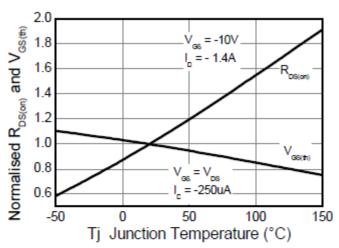




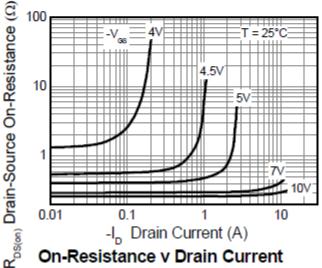


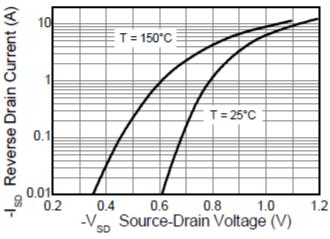


**Typical Transfer Characteristics** 

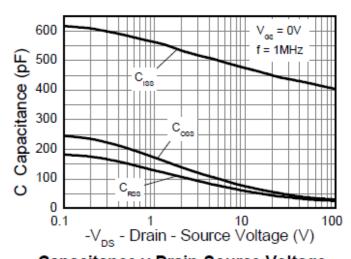


Normalised Curves v Temperature

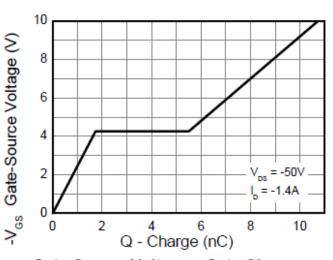




Source-Drain Diode Forward Voltage



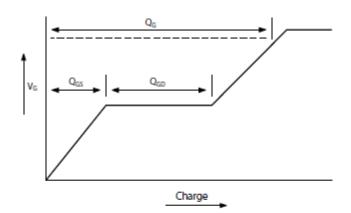
Capacitance v Drain-Source Voltage



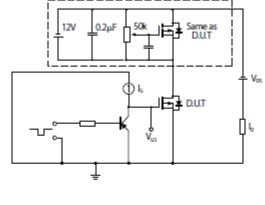
Gate-Source Voltage v Gate Charge



# **Test Circuits**

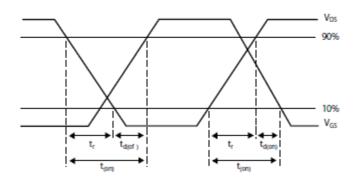


Basic gate charge waveform

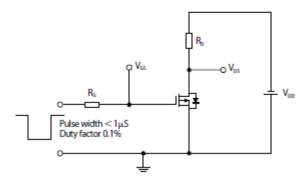


Current regulator

Gate charge test circuit



Switching time waveforms

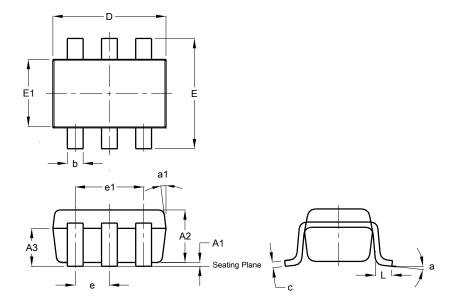


Switching time test circuit



# **Package Outline Dimensions**

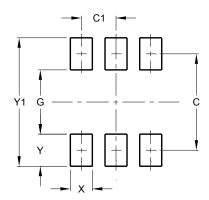
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
Е	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	Dimen	sions	in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
X	0.55
Υ	0.80
Y1	3 20



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